



MMDT2907A

DUAL PNP GENERAL PURPOSE SWITCHING TRANSISTOR

VOLTAGE 60 Volts **POWER** 150 mW

SOT-363 Unit: inch (mm)

FEATURES

- PNP epitaxial silicon, planar design
- Collector-emitter voltage $V_{CE} = -60V$
- Collector current $I_C = -600mA$
- In compliance with EU RoHS 2002/95/EC directives

MECHANICAL DATA

- Case: SOT-363
- Terminals : Solderable per MIL-STD-750, Method 2026
- Apporx. Weight: 0.0002 ounce, 0.006 gram
- Device Marking : M7A

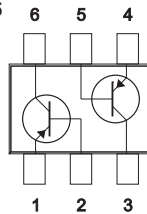
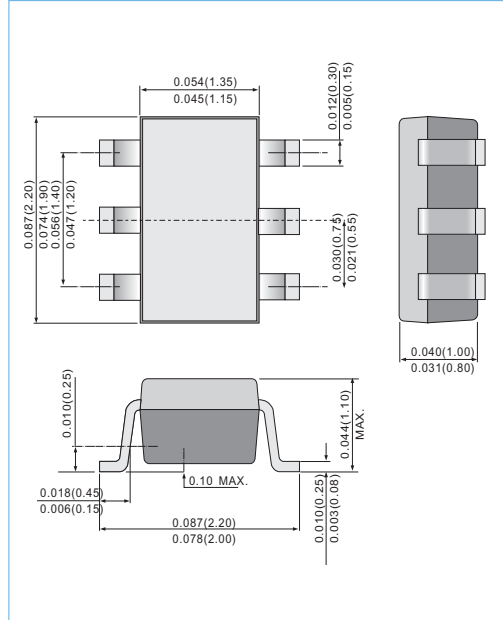


Fig.53



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Units
Collector-Emitter Voltage	V_{CEO}	-60	V
Collector-Base Voltage	V_{CBO}	-60	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Collector Current-Continuous	I_C	-600	mA

THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Units
Max Power Dissipation (Note 1)	P_{TOT}	150	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	830	$^{\circ}C / W$
Storage Temperature	T_{STG}	-55 to +150	$^{\circ}C$
Junction Temperature	T_J	-55 to +150	$^{\circ}C$

Note 1 : Transistor mouted on FR-5 board 1.0 x 0.75 x 0.062 in.



MMDT2907A

ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Units
Collector-Emitter Breakdown Voltage	V _(BR) CEO	I _C =-10mA, I _B =0	-60	-	-	V
Collector-Base Breakdown Voltage	V _(BR) CBO	I _C =-10μA, I _E =0	-60	-	-	V
Emitter-Base Breakdown Voltage	V _(BR) EBO	I _E =-10μA, I _C =0	-5.0	-	-	V
Base Cutoff Current	I _{BL}	V _{CE} =-30V, V _{EB} =-0.5V	-	-	-50	nA
Collector Cutoff Current	I _{CEX}	V _{CE} =-30V, V _{EB} =-0.5V	-	-	-50	nA
	I _{CBO}	V _{CE} =-50V, I _E =0	-	-	-10	nA
		V _{CE} =-50V, I _E =0 T _J =125°C	-	-	-10	μA
DC Current Gain	h _{FE}	I _C =-0.1mA, V _{CE} =-10V I _C =-1.0mA, V _{CE} =-10V I _C =-10mA, V _{CE} =-10V I _C =-150mA, V _{CE} =-10V I _C =-500mA, V _{CE} =-10V	75 100 100 100 50	- - - - -	- - - 300 -	-
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C =-150mA, I _B =-15mA I _C =-500mA, I _B =-50mA	- -	- -	-0.4 -1.6	V
Base-Emitter Saturation Voltage	V _{BE(SAT)}	I _C =-150mA, I _B =-15mA I _C =-500mA, I _B =-50mA	- -	- -	-1.3 -2.6	V
Collector-Base Capacitance	C _{CBO}	V _{CB} =-10V, I _E =0, f=1MHz	-	-	8.0	pF
Emitter-Base Capacitance	C _{EBO}	V _{CB} =-2V, I _C =0, f=1MHz	-	-	30	pF
Current Gain-Bandwidth Product	F _T	I _C =-50mA, V _{CE} =-20V, f=100MHz	200	-	-	MHz
Turn-On Time	t _{on}	V _{CC} =-30V, V _{BE} =-0.5V, I _C =-150mA, I _B =-15mA	-	-	45	ns
Delay Time	t _d	V _{CC} =-30V, V _{BE} =-0.5V, I _C =-150mA, I _B =-15mA	-	-	10	ns
Rise Time	t _r	V _{CC} =-30V, V _{BE} =-0.5V, I _C =-150mA, I _B =-15mA	-	-	40	ns
Turn-Off Time	t _{off}	V _{CC} =-6V, I _C =-150mA, I _{B1} =I _{B2} =-15mA	-	-	100	ns
Storage Time	t _s	V _{CC} =-6V, I _C =-150mA, I _{B1} =I _{B2} =-15mA	-	-	80	ns
Fall Time	t _f	V _{CC} =-6V, I _C =-150mA, I _{B1} =I _{B2} =-15mA	-	-	30	ns



MMDT2907A

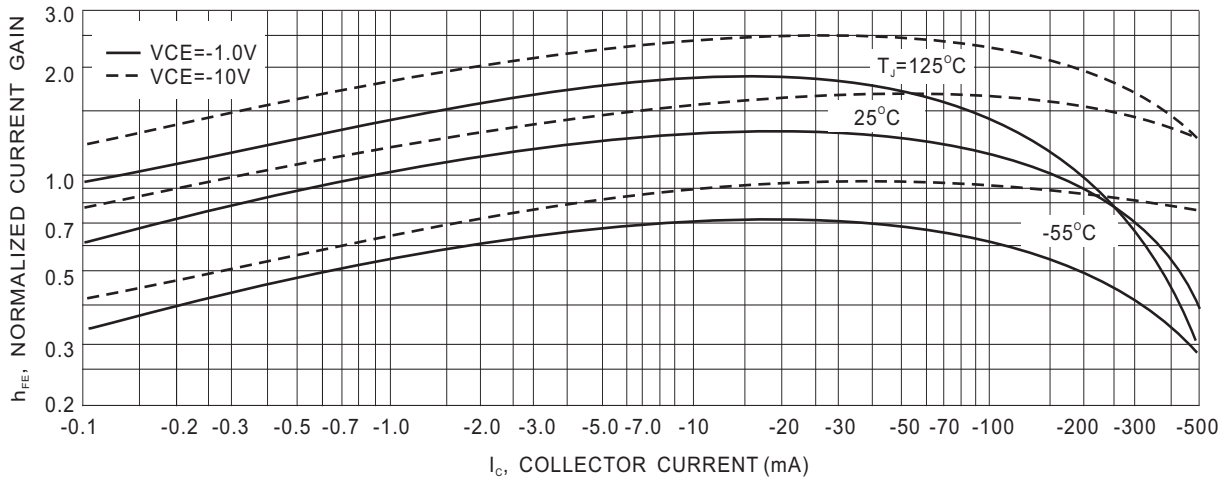


Fig.1-DC Current Gain

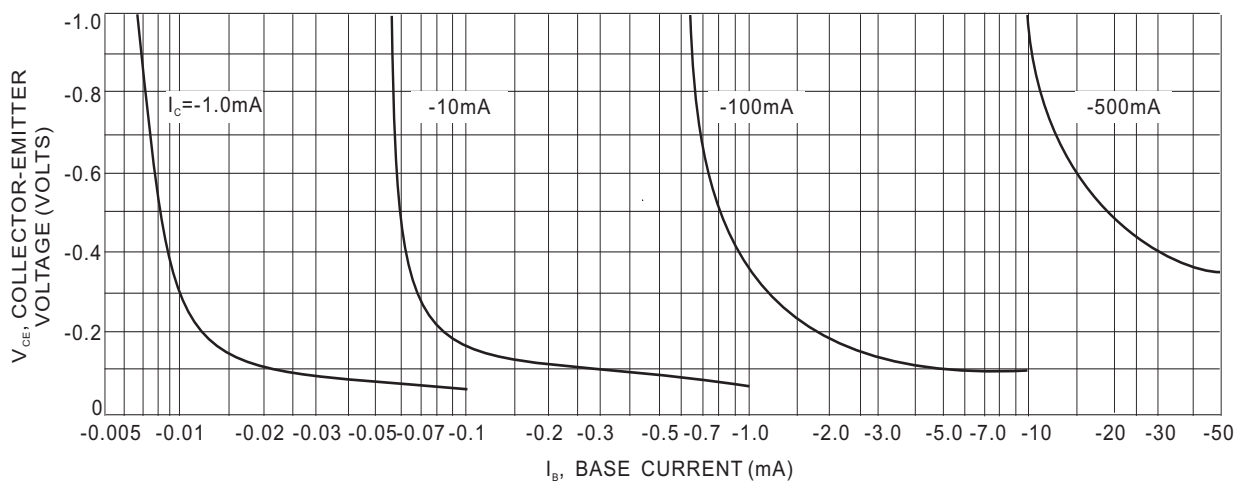


Fig.2-Collector Saturation Region

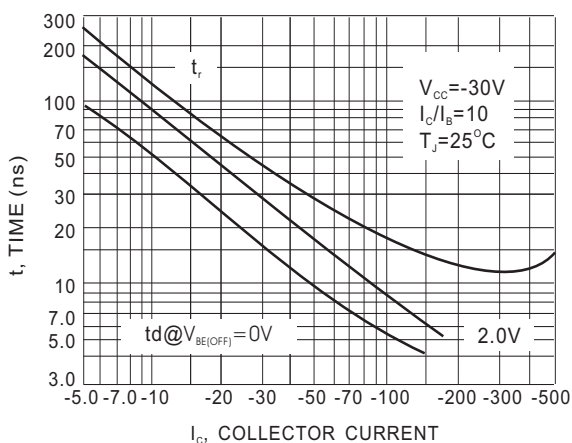


Fig.3-Turn-On Time

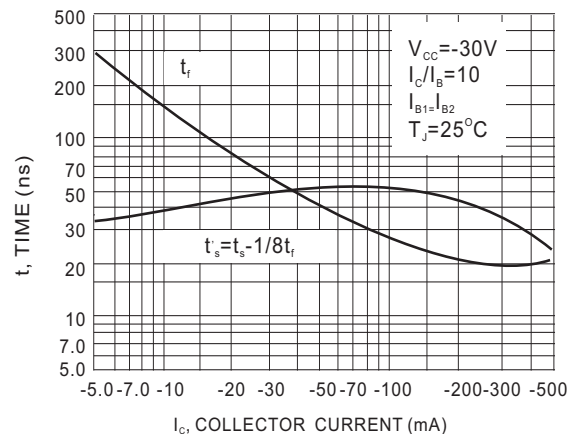


Fig.4-Turn-Off Time



MMDT2907A

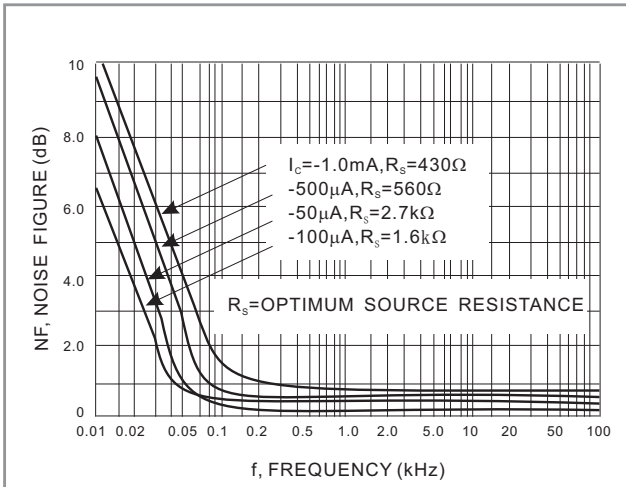


Fig.5-Frequency Effects

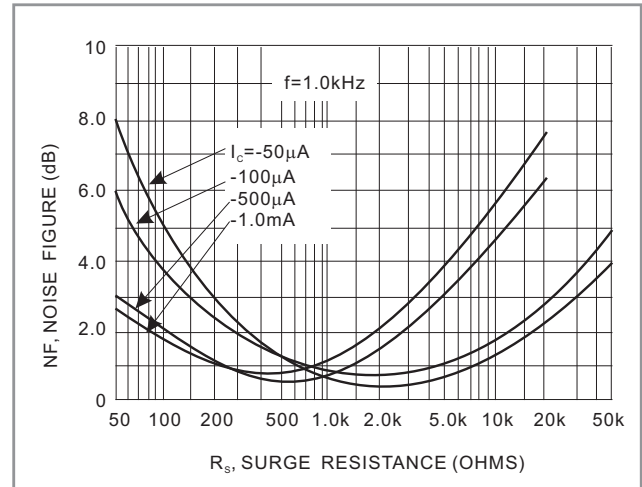


Fig.6-Source Resistance Effects

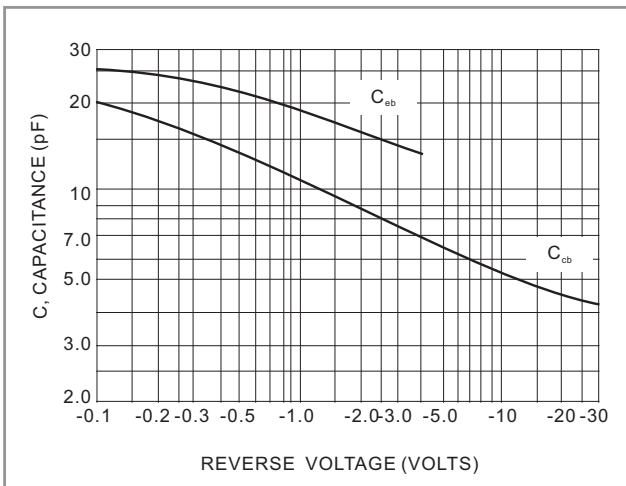


Fig.7-Capacitances

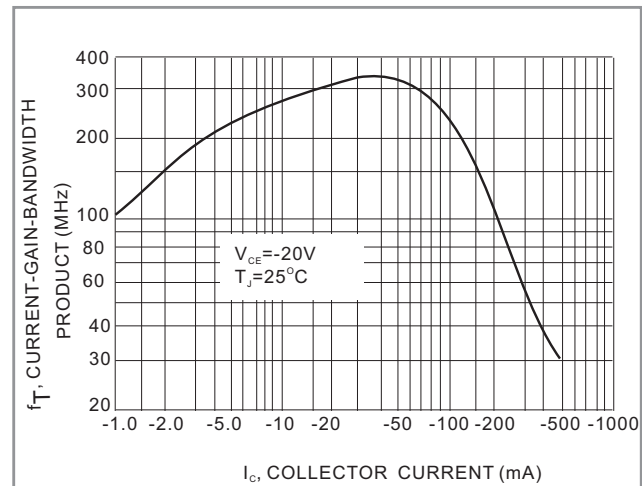


Fig.8-Current-Gain-Bandwidth Product

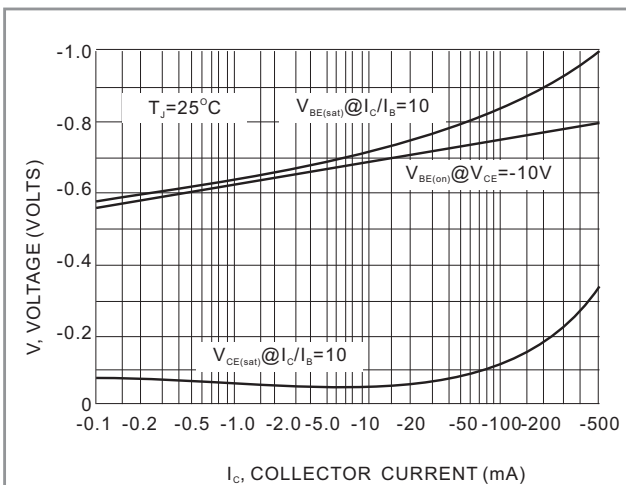


Fig.9-On Voltage

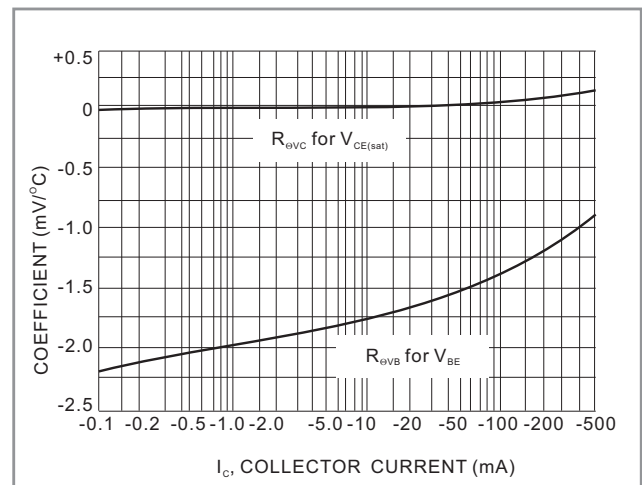
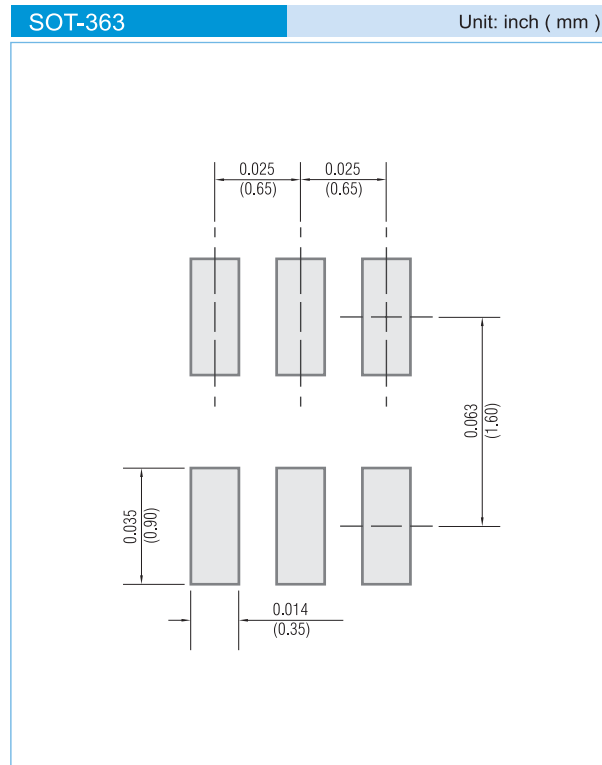


Fig.10-Temperature Coefficients



MMDT2907A

MOUNTING PAD LAYOUT



ORDER INFORMATION

- Packing information
 - T/R - 10K per 13" plastic Reel
 - T/R - 3K per 7" plastic Reel

LEGAL STATEMENT

Copyright PanJit International, Inc 2010

The information presented in this document is believed to be accurate and reliable. The specifications and information herein are subject to change without notice. Pan Jit makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose. Pan Jit products are not authorized for use in life support devices or systems. Pan Jit does not convey any license under its patent rights or rights of others.